

Silicon NPN Power Transistors

2SC4878

DESCRIPTION

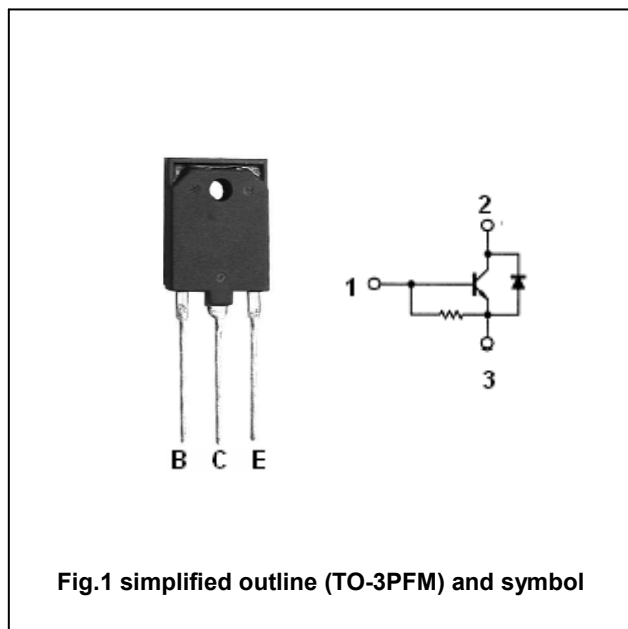
- With TO-3PFM package
- High breakdown voltage
- High speed switching
- Built-in damper diode

APPLICATIONS

- Color TV horizontal deflection output
- Color display horizontal deflection output

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		10	A
P _C	Collector power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	800			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =8A ; I _B =1.6A			5.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =8A ; I _B =1.6A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0	50		250	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	8			
h _{FE-2}	DC current gain	I _C =8A ; V _{CE} =5V	5			

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PACKAGE OUTLINE

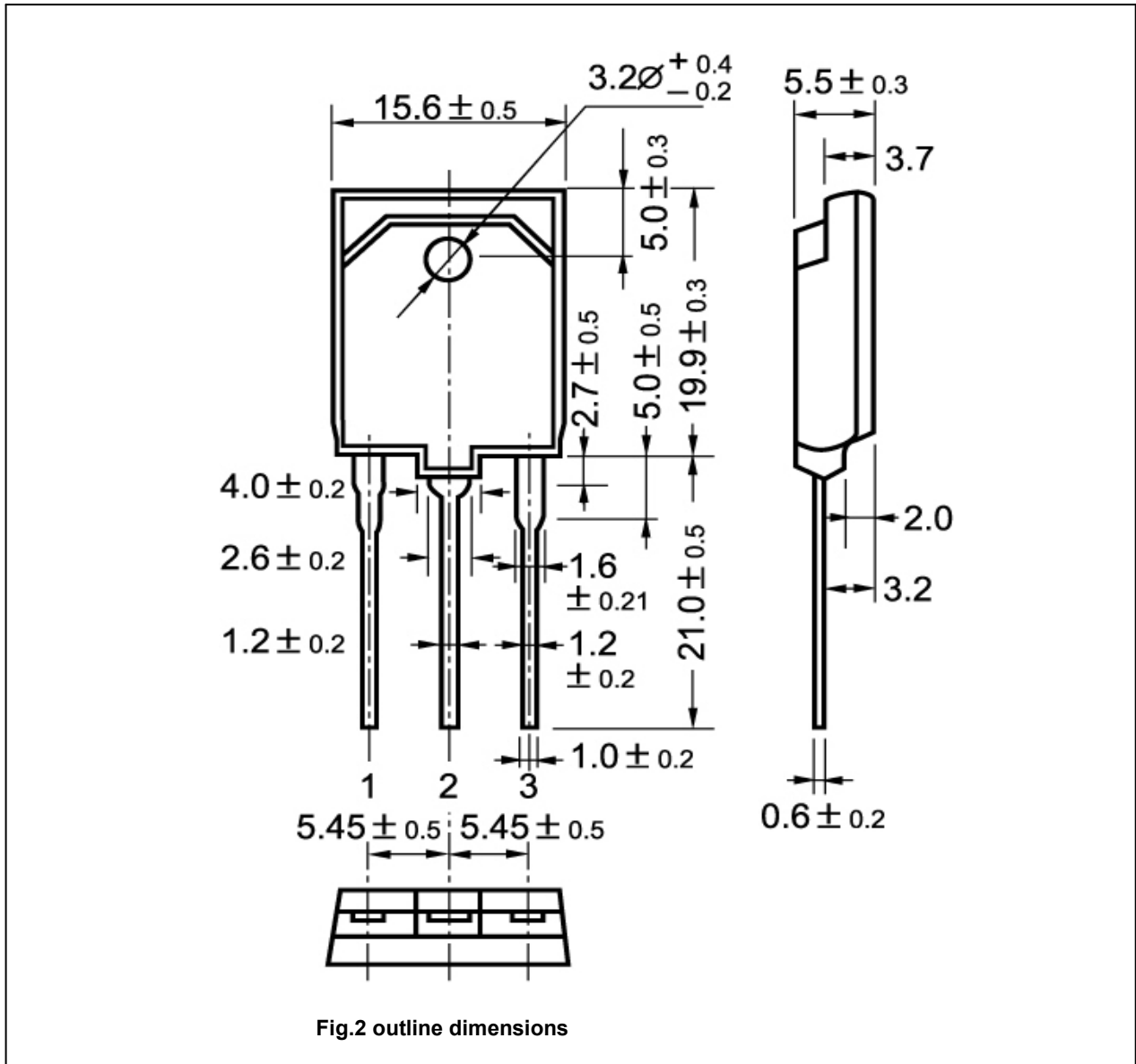


Fig.2 outline dimensions